Elektronische Bauelemente

2SB1274

-3A , -60V

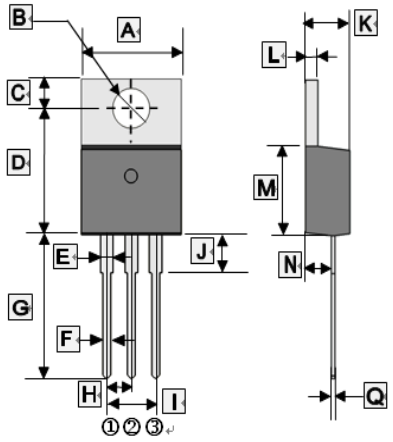
PNP Plastic Encapsulated Transistor

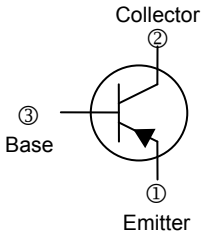
RoHS Compliant Product
A suffix of "-C" specifies halogen & lead-free

FEATURES

- General Purpose Switching and Amplification.
- Wide ASO (Adoption of MBIT Process)
- Low Saturation Voltage.

TO-220J





REF.	Millimeter Min.	Millimeter Max.	REF.	Millimeter Min.	Millimeter Max.
A	10.010	10.350	I	4.980	5.180
B	3.735	3.935	J	3.560	3.960
C	2.590	2.890	K	4.470	4.670
D	12.060	12.460	L	1.200	1.400
E	1.170	1.370	M	8.500	8.900
F	0.710	0.910	N	2.520	2.820
G	13.400	13.800	Q	0.330	0.650
H	2.540 TYP.				

ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise specified)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-60	V
Collector to Emitter Voltage	V_{CEO}	-60	V
Emitter to Base Voltage	V_{EBO}	-6	V
Collector Current - Continuous	I_C	-3	A
Collector Power Dissipation	P_C	2	W
Junction, Storage Temperature	T_J, T_{STG}	150, -55~150	°C

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test condition
Collector to Base Breakdown Voltage	$V_{(BR)CBO}$	-60	-	-	V	I_C= -1mA, I_E=0
Collector to Emitter Breakdown Voltage	$V_{(BR)CEO}$	-60	-	-	V	I_C= -5mA, I_B=0
Emitter to Base Breakdown Voltage	$V_{(BR)EBO}$	-6	-	-	V	I_E= -1mA, I_C=0
Collector Cut-Off Current	I_{CBO}	-	-	-0.1	μA	V_{CB}= -40V, I_E=0
Emitter Cut-Off Current	I_{EBO}	-	-	-0.1	μA	V_{EB}= -4V, I_C=0
DC Current Gain	h_{FE}	100	-	200		V_{CE}= -5V, I_C= -500mA
		20	-	-		V_{CE}= -5V, I_C= -3A
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	-	-	-1	V	I_C= -2A, I_B= -200mA
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	-	-	-1	V	V_{CE}= -5V, I_C= -500mA
Transition Frequency	f_T	-	100	-	MHz	V_{CE}= -5V, I_C= -500mA
Collector output capacitance	C_{ob}	-	60	-	pF	V_{CB}= -10V, I_E=0, f=1MHz